

P4.3021 Deposition and characterization of SiO_x-like thin films from HMDSO mixtures plasmas

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See the full abstract here:

<http://ocs.ciemat.es/EPS2019ABS/pdf/P4.3021.pdf>

Plasma polymerization of organosilanes is a valuable method for depositing both inorganic SiO₂-like films, which have found many applications in microelectronics and optics, and polymer-like SiO_x films, suitable for barrier films in food packaging and corrosion protection layers. In this work, SiO_x-like films were deposited on silicon and on aluminum substrates starting from HMDSO as precursor with different reactive gases (O₂ and/or Ar) [1]. Thin film morphology depends on growth process, two different chemical vapour deposition techniques have been employed: Plasma Assisted Supersonic Jet Deposition (PASJD) and Plasma Enhanced CVD (PECVD). The former is a technique which splits the deposition process into two steps: the precursor dissociation by a radio frequency (RF) inductively coupled plasma (ICP) and then nanoparticles acceleration and assembly on a substrate by means of a supersonic in-seminated jet [2]. The latter is one of the techniques allowing industrial-scale deposition of high-quality coatings. The reacting gases are also ionized by an RF inductively coupled discharge and the substrate is placed within a diffuse plasma region. Correlation between different operating conditions (such as the effect of HMDSO/O₂ ratio, total treatment pressure and growth time) and the resulting surface properties were also discussed. The structure and bondings in the deposited films were studied by means of Fourier transform infrared (FTIR) spectroscopy. The thickness of the deposited films was deduced applying a mask on the substrate and measuring the surface roughness with a mechanical profilometer. Films morphology and nano-structures were analyzed by scanning electron microscopy (SEM). Thermal annealing was performed, the effects induced on film composition and chemical structure were therefore evaluated. The capability of controlling the film composition by varying operating conditions opens interesting perspectives. A potential research direction of this study worth exploring is to electro-chemically reduce the SiO_x-like films to obtain a nano- or fine micro-structured surface layer, providing a novel Black-Silicon fabrication process.

References

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- [2] Biganzoli, I., Fumagalli, F., Di Fonzo, F., Barni, R. and Riccardi, C., *Journal of Modern Physics*, 3(10), (2012)

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